

Vishay Siliconix

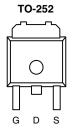
RoHS

COMPLIANT

HALOGEN FREE

P-Channel 40 V (D-S) MOSFET

PRODUCT SUMMARY					
V _{DS} (V)	R _{DS(on)} (Ω) Max.	I _D (A)	Q _g (Typ.)		
- 40	0.0162 at V _{GS} = - 10 V	- 36	67		
- 40	0.0230 at V _{GS} = - 4.5 V	- 24	07		



Top View

Ordering Information: SUD45P04-16P-GE3 (Lead (Pb)-free and Halogen-free)

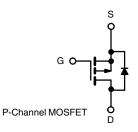
Drain Connected to Tab

FEATURES

- Halogen-free According to IEC 61249-2-21 • Definition
- TrenchFET[®] Power MOSFET •
- 100 % R_a and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Power Switch
- Load Switch in High Current Applications
- **DC/DC** Converters



ABSOLUTE MAXIMUM RATINGS	(T _C = 25 °C, unless ot	nerwise noted)			
Parameter	Symbol	Limit	Unit		
Drain-Source Voltage	V _{DS}	- 40	V		
Gate-Source Voltage		V _{GS}	± 20	- V	
Continuous Drain Current (T_{1} = 150 °C)	T _C = 25 °C	1-	- 36		
Continuous Drain Current $(1) = 150^{\circ}$ C)	T _C = 70 °C	I _D	- 29	A	
Pulsed Drain Current (t = 300 μs)		I _{DM}	- 100	A	
Avalanche Current	I _{AS}	- 32	1		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	51	mJ	
	T _C = 25 °C	Р	41.7 ^b	14/	
Maximum Power Dissipation ^a	T _A = 25 °C ^c	- P _D -	2.1	- w	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	60	°C/W		
Junction-to-Case (Drain)	R _{thJC}	3	C/VV		

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

Vishay Siliconix



Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{DS} = 0 V, I_{D} = -250 \mu A$	- 40		v		
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_{D} = -250 \ \mu A$	- 1		- 2.5	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA	
		$V_{DS} = -40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$			- 1		
Zero Gate Voltage Drain Current	I _{DSS}	V_{DS} = - 40 V, V_{GS} = 0 V, T_{J} = 125 °C			- 50		
		$V_{DS} = -40 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 150 ^{\circ}\text{C}$			- 250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \le$ - 10 V, V_{GS} = - 10 V	- 50			Α	
	D	V _{GS} = - 10 V, I _D = - 14 A		0.0135	0.0162	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V _{GS} = - 4.5 V, I _D = - 12 A		0.0190	0.0230	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = - 20 V, I _D = - 14 A		40		S	
Dynamic ^b		· · · · ·					
Input Capacitance	C _{iss}			2765		pF	
Output Capacitance	C _{oss}	$V_{GS} = 0 V$, $V_{DS} = -20 V$, f = 1 MHz		330			
Reverse Transfer Capacitance	C _{rss}			280			
Total Gate Charge ^c	Qg			67	100	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = -20 \text{ V}, V_{GS} = -10 \text{ V}, I_{D} = -14 \text{ A}$		13.5			
Gate-Drain Charge ^c	Q _{gd}			14			
Gate Resistance	Rg	f = 1 MHz	0.5	2.5	5	Ω	
Turn-On Delay Time ^c	t _{d(on)}			10	20		
Rise Time ^c	t _r	V_{DD} = - 20 V, R_L = 2 Ω		11	20		
Turn-Off Delay Time ^c	t _{d(off)}	$I_D \cong$ - 10 A, V_{GEN} = - 10 V, R_g = 1 Ω		42	63	ns	
Fall Time ^c	t _f			12	20		
Drain-Source Body Diode Ratings an	nd Characteri	stics T _C = 25 °C ^b					
Continuous Current	۱ _S				- 36	^	
Pulsed Current	I _{SM}				- 100	A	
Forward Voltage ^a	V _{SD}	I _F = - 10 A, V _{GS} = 0 V		- 0.8	- 1.5	V	
Reverse Recovery Time	t _{rr}			38	57	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = - 10 A, dI/dt = 100 A/μs		2.3	3.5	А	
Reverse Recovery Charge	Q _{rr}	1 1		40	60	nC	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

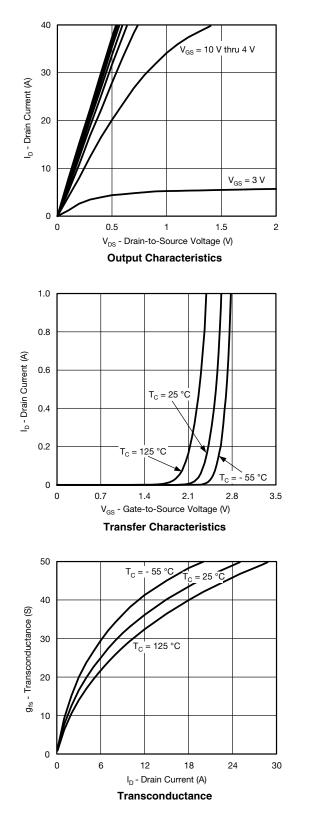
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

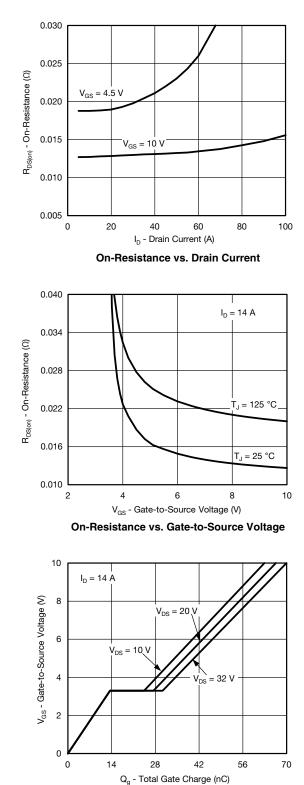
This document is subject to change without notice. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



Vishay Siliconix







Gate Charge

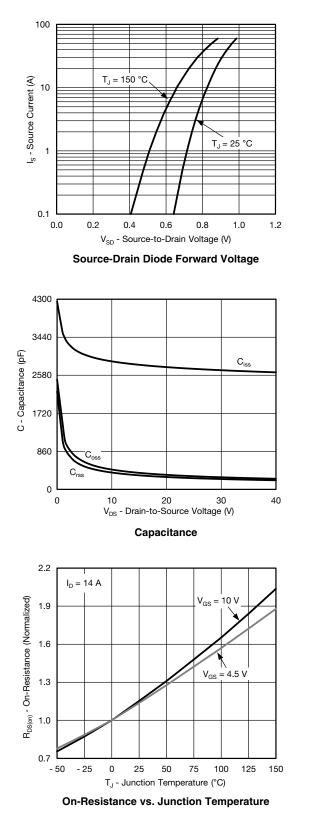
Document Number: 63372 S11-1657-Rev. A, 15-Aug-11 This document is subject to change without notice. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000

3

Vishay Siliconix

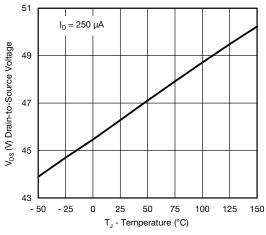


TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

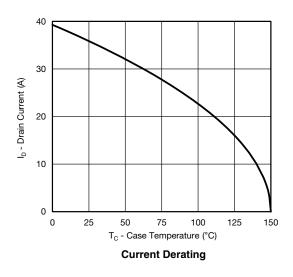


2.3 I_D = 250 μA 2.0 V_{GS(th)} (V) 1.7 1.4 1.1 - 50 - 25 100 150 0 25 50 75 125 T_J - Temperature (°C)

Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



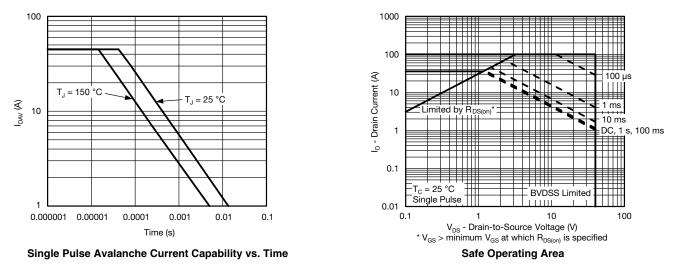
www.vishay.com 4 Document Number: 63372 S11-1657-Rev. A, 15-Aug-11

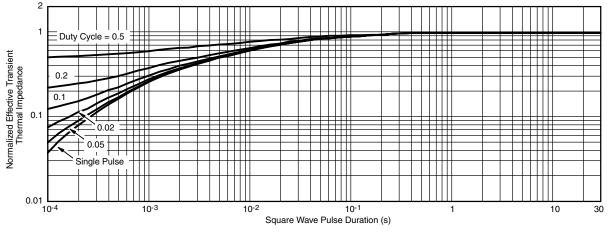
This document is subject to change without notice. THE PRODUCTS DESCRIBED HEREIN AND THIS DOCUMENT ARE SUBJECT TO SPECIFIC DISCLAIMERS, SET FORTH AT www.vishay.com/doc?91000



Vishay Siliconix

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)





Normalized Thermal Transient Impedance, Junction-to-Case

Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package/tape drawings, part marking, and reliability data, see www.vishay.com/ppg?63372.

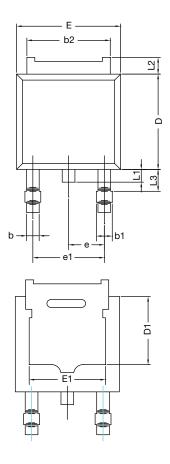
Document Number: 63372 www.vishay.com S11-1657-Rev. A, 15-Aug-11 5

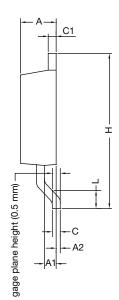


Package Information

Vishay Siliconix

TO-252AA CASE OUTLINE





	MILLIN	IETERS	INCHES		
DIM.	MIN.	MAX.	MIN.	MAX.	
А	2.21	2.38	0.087	0.094	
A1	0.89	1.14	0.035	0.045	
A2	0.030	0.127	0.001	0.005	
b	0.71	0.88	0.028	0.035	
b1	0.76	1.14	0.030	0.045	
b2	5.23	5.44	0.206	0.214	
С	0.46	0.58	0.018	0.023	
C1	0.46	0.58	0.018	0.023	
D	5.97	6.22	0.235	0.245	
D1	4.10	4.45	0.161	0.175	
E	6.48	6.73	0.255	0.265	
E1	4.49	5.50	0.177	0.217	
е	2.28 BSC		0.090 BSC		
e1	4.57	BSC	SC 0.180 BSC		
Н	9.65	10.41	0.380	0.410	
L	1.40	1.78	0.055	0.070	
L1	0.64	1.02	0.025	0.040	
L2	0.89	1.27	0.035	0.050	
L3	1.15	1.52	0.040	0.060	
ECN: T11- DWG: 534	0110-Rev. L, ⁻ 7	18-Apr-11			

Note

• Dimension L3 is for reference only.

www.vishay.com

1



Vishay Siliconix

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads Dimensions in Inches/(mm)

Return to Index



Vishay

Disclaimer

ALL PRODUCT, PRODUCT SPECIFICATIONS AND DATA ARE SUBJECT TO CHANGE WITHOUT NOTICE TO IMPROVE RELIABILITY, FUNCTION OR DESIGN OR OTHERWISE.

Vishay Intertechnology, Inc., its affiliates, agents, and employees, and all persons acting on its or their behalf (collectively, "Vishay"), disclaim any and all liability for any errors, inaccuracies or incompleteness contained in any datasheet or in any other disclosure relating to any product.

Vishay makes no warranty, representation or guarantee regarding the suitability of the products for any particular purpose or the continuing production of any product. To the maximum extent permitted by applicable law, Vishay disclaims (i) any and all liability arising out of the application or use of any product, (ii) any and all liability, including without limitation special, consequential or incidental damages, and (iii) any and all implied warranties, including warranties of fitness for particular purpose, non-infringement and merchantability.

Statements regarding the suitability of products for certain types of applications are based on Vishay's knowledge of typical requirements that are often placed on Vishay products in generic applications. Such statements are not binding statements about the suitability of products for a particular application. It is the customer's responsibility to validate that a particular product with the properties described in the product specification is suitable for use in a particular application. Parameters provided in datasheets and/or specifications may vary in different applications and performance may vary over time. All operating parameters, including typical parameters, must be validated for each customer application by the customer's technical experts. Product specifications do not expand or otherwise modify Vishay's terms and conditions of purchase, including but not limited to the warranty expressed therein.

Except as expressly indicated in writing, Vishay products are not designed for use in medical, life-saving, or life-sustaining applications or for any other application in which the failure of the Vishay product could result in personal injury or death. Customers using or selling Vishay products not expressly indicated for use in such applications do so at their own risk. Please contact authorized Vishay personnel to obtain written terms and conditions regarding products designed for such applications.

No license, express or implied, by estoppel or otherwise, to any intellectual property rights is granted by this document or by any conduct of Vishay. Product names and markings noted herein may be trademarks of their respective owners.

Material Category Policy

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as RoHS-Compliant fulfill the definitions and restrictions defined under Directive 2011/65/EU of The European Parliament and of the Council of June 8, 2011 on the restriction of the use of certain hazardous substances in electrical and electronic equipment (EEE) - recast, unless otherwise specified as non-compliant.

Please note that some Vishay documentation may still make reference to RoHS Directive 2002/95/EC. We confirm that all the products identified as being compliant to Directive 2002/95/EC conform to Directive 2011/65/EU.

Vishay Intertechnology, Inc. hereby certifies that all its products that are identified as Halogen-Free follow Halogen-Free requirements as per JEDEC JS709A standards. Please note that some Vishay documentation may still make reference to the IEC 61249-2-21 definition. We confirm that all the products identified as being compliant to IEC 61249-2-21 conform to JEDEC JS709A standards.